

## **STPS40M100C**

### Power Schottky rectifier

#### **Features**

- High current capability
- Avalanche rated
- Low forward voltage drop current
- High frequency operation

#### **Description**

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB and I<sup>2</sup>PAK, this device is intended to be used in notebook, game station and desktop adaptors, providing in these applications a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	2 x 20 A
V <sub>RRM</sub>	100 V
T <sub>j</sub> (max)	150 °C
V <sub>F</sub> (typ)	0.420 V

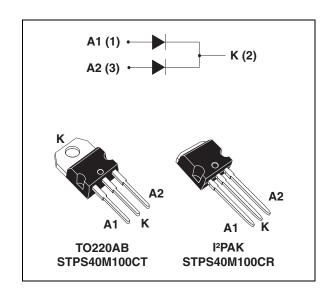
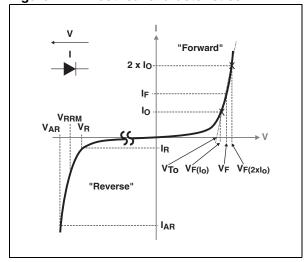


Figure 1. Electrical characteristics (a)



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a.  $V_{ARM}$  and  $I_{ARM}$  must respect the reverse safe operating area defined in *Figure 11*  $V_{AR}$  and  $I_{AR}$  are pulse measurements ( $t_p < 1~\mu s$ ).  $V_R$ ,  $I_R$ ,  $V_{RRM}$  and  $V_F$ , are static characteristics

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#### 1 Characteristics

Table 2. Absolute ratings (limiting values per diode at 25 °C unless otherwise stated)

Symbol	Parameter				Unit
$V_{RRM}$	Repetitive peak reverse voltage			100	V
I <sub>F(RMS)</sub>	Forward current rms			60	Α
1	Average forward current $\delta = 0.5$	T <sub>c</sub> = 125 °C	Per diode	20	Α
I <sub>F(AV)</sub>		T <sub>c</sub> = 120 °C	Per package	40	^
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			530	Α
P <sub>ARM</sub> <sup>(1)</sup>	Repetitive peak avalanche power $t_p = 1 \mu s T_j = 25  ^{\circ}C$			23 200	W
V <sub>ARM</sub> (2)	Maximum repetitive peak avalanche voltage $t_p < 1 \mu s$ $T_j < 150 °C$ , $I_{AR} < 58 A$			120	V
V <sub>ASM</sub> (2)	Maximum single pulse peak avalanche voltage $ t_p < 1 \mu s$ $T_j < 150$ °C, $I_{AR} < 58$ A			120	V
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C
T <sub>j</sub>	Maximum operating junction temperature (3)			150	°C

For temperature or pulse time duration deratings, refer to Figure 4. and Figure 5.. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

Table 3. Thermal resistance

Symbol		Parameter	Value	Unit
D	Junction to case	Per diode	1.4	°C/W
R <sub>th(j-c)</sub>	Junction to case	Total	0.95	C/VV
R <sub>th(c)</sub>	Coupling		0.5	°C/W

When diodes 1 and 2 are used simultaneously

 $T_j(diode\ 1) = P(diode\ 1) \times R_{th(j-c)}(Per\ diode) + P(diode\ 2) \times R_{th(c)}$ 

Table 4. Static electrical characteristics

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
	I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$	•	-	70	μΑ
<sub>I_</sub> (1)		T <sub>j</sub> = 125 °C		ı	15	70	mA
'R`´		T <sub>j</sub> = 25 °C	V <sub>R</sub> = 70 V	-	-	40	μΑ
		T <sub>j</sub> = 125 °C		-	7.5	40	mA
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 125 °C	I <sub>F</sub> = 5 A	-	0.415	0.500	٧
V (2)		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 10A	-	0.500	0.560	-
VF.		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 20 A	-	-	0.780	-
		T <sub>j</sub> = 125 °C		-	0.585	0.640	-

<sup>1.</sup> Pulse test:  $t_p = 5 \text{ ms}, \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 0.560 \times I_{F(AV)} + 0.004 \times I_{F}^{2}_{(RMS)}$$

<sup>2.</sup> Refer to Figure 11

<sup>3.</sup>  $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink

<sup>2.</sup> Pulse test:  $t_p = 380 \mu s$ ,  $\delta < 2\%$ 

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Figure 2. Average forward power dissipation Figure 3. Average forward current per diode versus average forward current versus ambient temperature (per diode)  $(\delta = 0.5)$ 

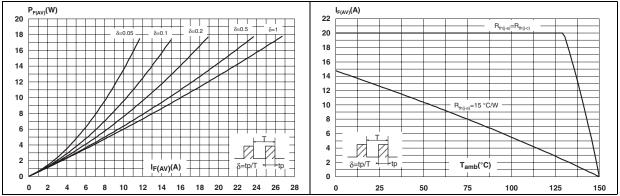


Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature

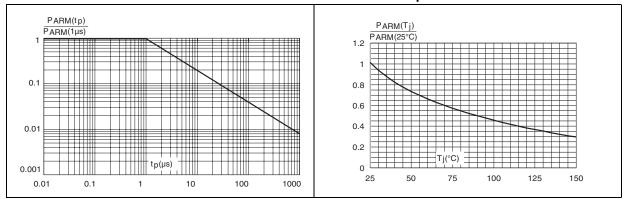
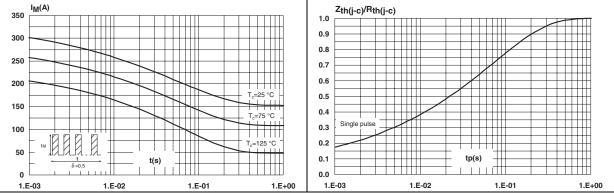


Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values per diode)

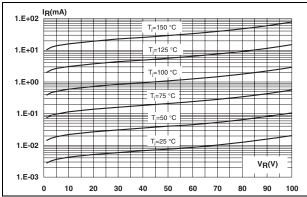
Figure 7. Relative variation of thermal impedance junction to case versus pulse duration



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Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)



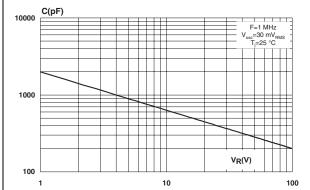
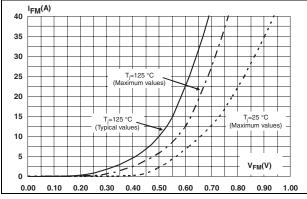
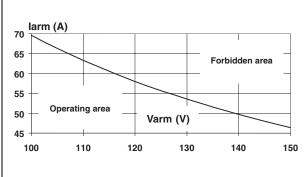


Figure 10. Forward voltage drop versus forward current (per diode)

Figure 11. Reverse safe operating area  $(t_p < 1 \mu s \text{ and } T_i < 150 \,^{\circ}\text{C})$ 





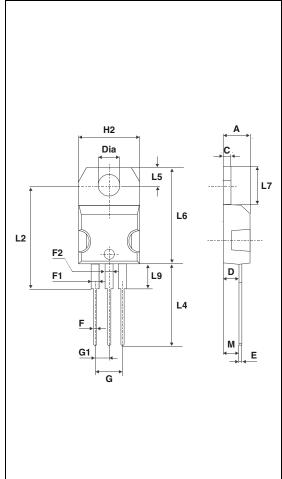
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## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: conduction
- Recommended torque value: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Table 5. TO-220AB dimensions

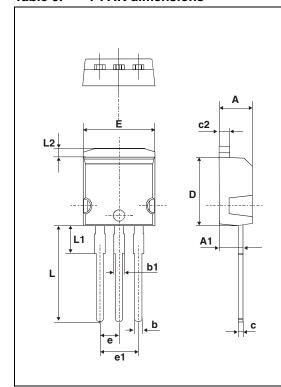


	Dimensions			
Ref.	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
С	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
Е	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393 0.409	
L2	16.4	typ.	0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
М	2.6	typ.	0.10	2 typ.
Diam.	3.75	3.85	0.147	0.151

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Mounting (soldering) the I2PAK metal slug (heatsink) with alloy, like a surface mount device, IS NOT PERMITTED. A standard through-hole mounting is mandatory.

Table 6. I<sup>2</sup>PAK dimensions



	Dimensions			
Ref.	Millimeters		Inc	hes
	Min.	Min. Max.		Max.
Α	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
С	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
е	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
Е	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

# 3 Ordering information

Table 7. Ordering information

Order code	Marking Package		Weight	Base qty	Delivery mode
STPS40M100CT	STPS40M100CT	TO-220AB	1.9 g	50	Tube
STPS40M100CR	STPS40M100CR	I <sup>2</sup> PAK	1.5 g	50	Tube

# 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
25-Mar-2009	1	First issue.
10-Apr-2010	2	Updated package graphics.
29-Apr-2010	3	Added I <sup>2</sup> PAK package. Updated weight in <i>Table 7</i> .

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